

MA6X126

Silicon epitaxial planar type

For switching circuits

■ Features

- Four-element contained in one package, allowing high-density mounting
- High breakdown voltage ($V_R = 80\text{ V}$)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Average forward current* ¹	$I_{F(AV)}$	100	mA
Peak forward current* ¹	I_{FM}	225	mA
Non-repetitive peak forward surge current* ^{1,2}	I_{FSM}	500	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *1 : Value for single diode

*2 : $t = 1\text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

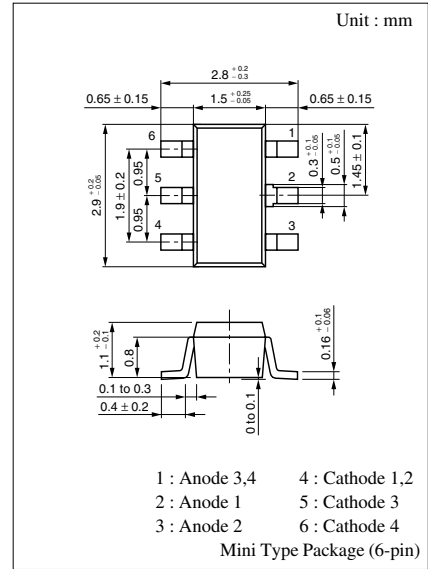
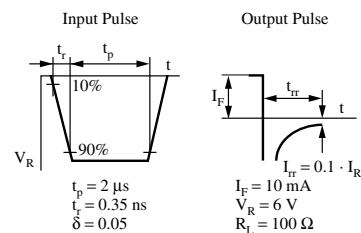
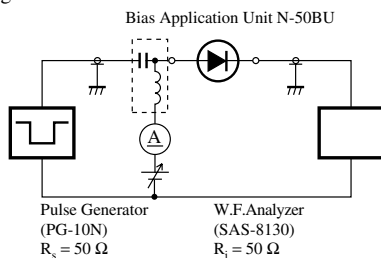
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75\text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100\ \mu\text{A}$	80			V
Terminal capacitance	C_{i1} * ¹	$V_R = 0\text{ V}, f = 1\text{ MHz}$			15	pF
	C_{i2} * ²	$V_R = 0\text{ V}, f = 1\text{ MHz}$			2	pF
Reverse recovery time* ³	t_{rr1} * ¹	$I_F = 10\text{ mA}, V_R = 6\text{ V}$			10	ns
	t_{rr2} * ²	$I_{rr} = 0.1 \cdot I_R, R_L = 100\ \Omega$			3	

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Between pins 1 and 5, Between pins 1 and 6

*2 : Between pins 4 and 2, Between pins 4 and 3

*3 : t_{rr} measuring circuit



Marking Symbol: M2S

Internal Connection

